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(54) **THIN FILM TRANSISTOR ASSEMBLY,
ARRAY SUBSTRATE METHOD OF
MANUFACTURING THE SAME, AND
DISPLAY DEVICE**

(58) **Field of Classification Search**
CPC .. H01L 21/336; H01L 29/786; H01L 27/1248;
H01L 27/1262
See application file for complete search history.

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(57) **ABSTRACT**

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The present disclosure discloses a thin film transistor assem-
bly, an array substrate and a method of manufacturing the
same, and a display device including the array substrate. The
array substrate includes a substrate; a plurality of thin film
transistors formed on the substrate; and a plurality of light
shielding layers, each of the light shielding layers being
arranged between a source electrode and a drain electrode of
the thin film transistor and configured to block light from the
exterior from illuminating an active layer of the thin film
transistor. The light shielding layer and the source electrode
and the drain electrode of the thin film transistor are formed
in the same layer on the substrate. As the light shielding
layer, the source electrode and the drain electrode of the thin
film transistor and a data line may be formed on the substrate

(Continued)

(52) **U.S. Cl.**

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